

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A mask for reducing proximity effect, comprising:

a plurality of line-shaped features;

a plurality of groups of first assist features, each group of first assist features positioned between two adjacent line-shaped features, wherein the first assist feature is approximately rectangular in shape and the width of the first assist feature is larger than the length of the first assist feature; and

a plurality of second assist features, each of the plurality of second assist features positioned between one of the plurality of line-shaped features and one group of first assist features, wherein the width of the second assist feature is smaller than two-fifths but larger than one-fourth of the wavelength of an exposure source.

2. (Original) The mask for reducing proximity effect of Claim 1, wherein the width of the second assist feature is equal or close to the length of the first assist feature.
3. (Original) The mask for reducing proximity effect of Claim 1, wherein the space between the group of first assist features and the second assist feature is equal to or larger than the width of the second assist feature.
4. (Original) The mask for reducing proximity effect of Claim 1, wherein the space between the line-shaped feature and the second assist feature is larger than the width of the line-shaped feature.
5. (Cancelled)

6. (Original) The mask for reducing proximity effect of Claim 1, wherein the line-shaped feature corresponds to an isolation trench pattern to be formed on a wafer.
7. (Currently Amended) A mask for reducing proximity effect, comprising:  
a plurality of line-shaped features; and  
a plurality of groups of assist features, each group of assist features positioned between two adjacent line-shaped features, wherein the assist feature is approximately rectangular in shape, and the width of the assist feature is larger than the length of the assist feature, and the length of the assist feature is smaller than two-fifths but larger than one-fourth of the wavelength of an exposure source.
8. (Original) The mask for reducing proximity effect of Claim 7, wherein the space between one of the plurality of line-shaped features and one group of assist feature is larger than the width of the line-shaped feature.
9. (Cancelled)
10. (Original) The mask for reducing proximity effect of Claim 7, wherein the space between the adjacent assist features is larger than the length of the assist feature.